

9P2811

Attorney's Docket No.: 10417-039001 / F51-125462M/HW



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Toshimitsu Taniguchi et al. Art Unit : 2811
Serial No. : 09/652,044 ↓ Examiner : Samuel A. Gebremariam
Filed : August 31, 2000
Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING
THEREOF

Commissioner for Patents
Washington, D.C. 20231

RESPONSE

In response to the action mailed June 5, 2002, please amend the application as follows
(unamended claims appear in small print and italics for ease of reference):

In the claims:

Please amend claims 6-8, 10-19, 22-24, 27-28 as follows:

DI
--6. (Amended) A method of manufacturing a semiconductor device comprising:
forming high concentration source/drain layers of the reverse conductive type in a
semiconductor layer of one conductive type;
forming a gate electrode on a channel layer located between the source and drain
layers; and
forming a body layer of one conductive type adjacent to the source layer and a
low concentration drain layer of the reverse conductive type formed between the channel
layer and the drain layer, wherein the body layer is formed only under the gate electrode,
and wherein forming a body layer of one conductive type comprises doping impurities of
one conductive type into said semiconductor layer by ion implantation.--

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